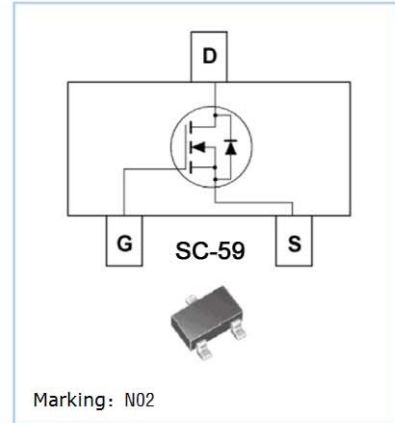


## Feature

- 20V/3.6A,  $R_{DS(ON)} = 80\text{m}\Omega$  (MAX) @ $V_{GS} = 4.5\text{V}$ .  
 $R_{DS(ON)} = 90\text{m}\Omega$  (MAX) @ $V_{GS} = 2.5\text{V}$ .
- Super High dense cell design for extremely low  $R_{DS(ON)}$ .
- Reliable and Rugged.
- SC-59 for Surface Mount Package.



## Applications

- Power Management  
 Portable Equipment and Battery Powered Systems.

## Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$  Unless Otherwise noted

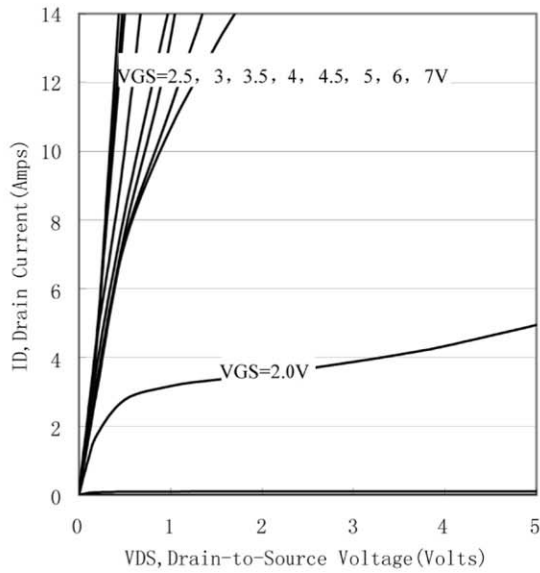
| Parameter                | Symbol   | Limit   | Units |
|--------------------------|----------|---------|-------|
| Drain-Source Voltage     | $V_{DS}$ | 20      | V     |
| Gate-Source Voltage      | $V_{GS}$ | $\pm 8$ | V     |
| Drain Current-Continuous | $I_D$    | 3.6     | A     |

## Electrical Characteristics

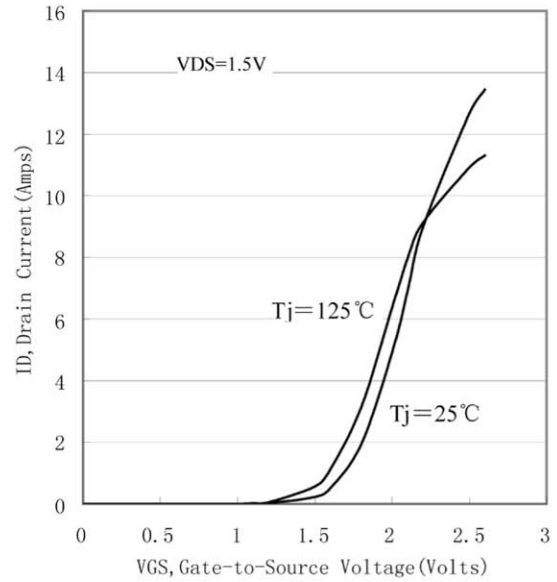
$T_A = 25^\circ\text{C}$  Unless Otherwise noted

| Parameter   | Symbol       | Test Conditions                            | Min | Typ. | Max  | Units            |
|---|--------------|--|-----|------|------|------------------|
| <b>Off Characteristics</b>                                    |              |  |     |      |      |                  |
| Drain to Source Breakdown Voltage                             | BVDSS        | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$ | 20  | -    | -    | V                |
| Zero-Gate Voltage Drain Current                               | $I_{DSS}$    | $V_{DS} = 12\text{V}, V_{GS} = 0\text{V}$  | -   | -    | 1    | $\mu\text{A}$    |
| Gate Body Leakage Current, Forward                            | $I_{GSSF}$   | $V_{GS} = 8\text{V}, V_{DS} = 0\text{V}$   | -   | -    | 100  | nA               |
| Gate Body Leakage Current, Reverse                            | $I_{GSSR}$   | $V_{GS} = -8\text{V}, V_{DS} = 0\text{V}$  | -   | -    | -100 | nA               |
| <b>On Characteristics</b>                                     |              |  |     |      |      |                  |
| Gate Threshold Voltage  | $V_{GS(th)}$ | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$    | 0.4 | -    | 1.3  | V                |
| Static Drain-source<br>On-Resistance                          | $R_{DS(ON)}$ | $V_{GS} = 4.5\text{V}, I_D = 3.6\text{A}$  | -   | 70   | 80   | $\text{m}\Omega$ |
|   |              | $V_{GS} = 2.5\text{V}, I_D = 3.1\text{A}$  | -   | 75   | 90   | $\text{m}\Omega$ |
| <b>Drain-Source Diode Characteristics and Maximum Ratings</b> |              |  |     |      |      |                  |
| Drain-Source Diode Forward Voltage                            | VSD          | $V_{GS} = 0\text{V}, I_S = 0.94\text{A}$   |     |      | 1.2  | V                |

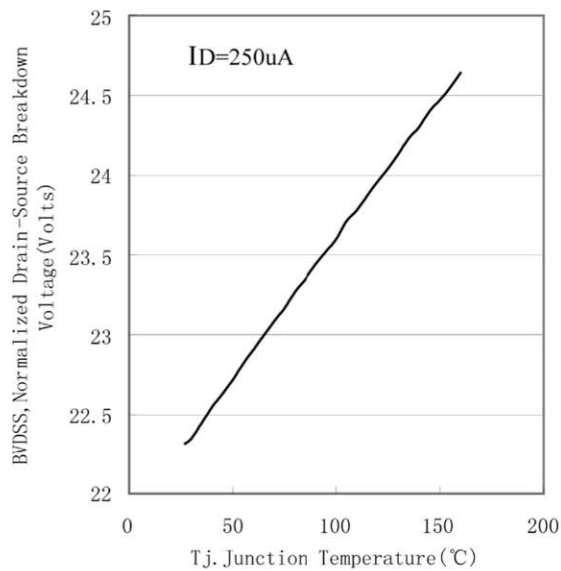
## Typical Characteristics



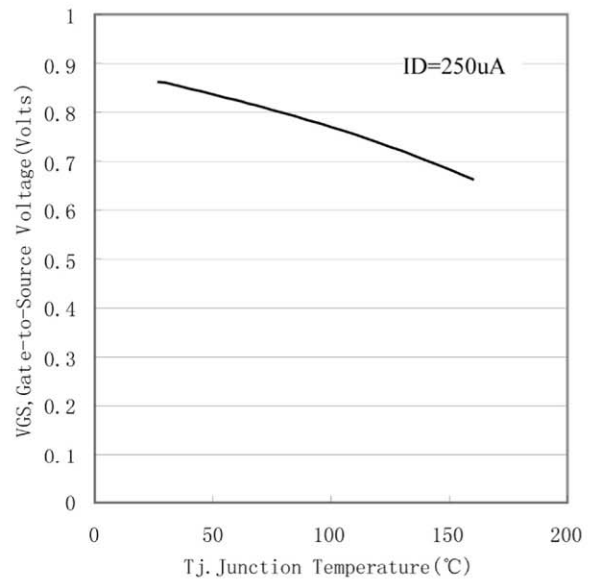
**Figure 1. Output Characteristics**



**Figure 2. Transfer Characteristics**

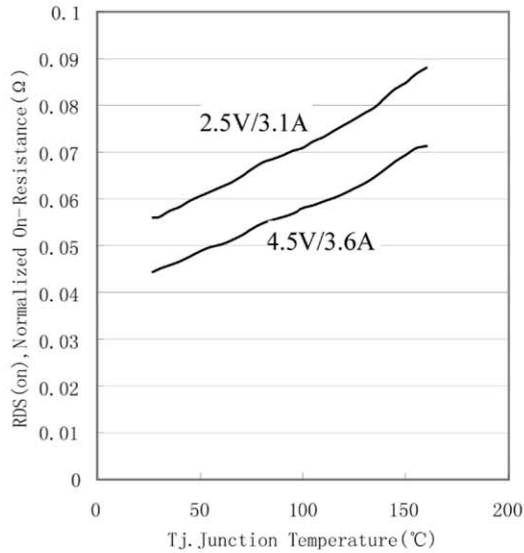


**Figure 3. Breakdown Voltage Variation with Temperature**

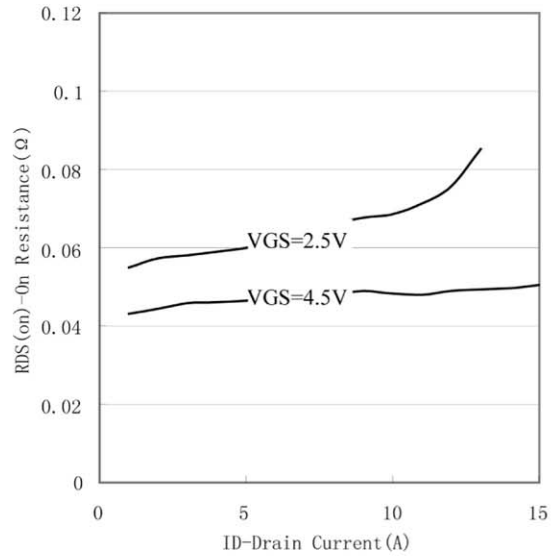


**Figure 4. Gate Threshold Variation with Temperature**

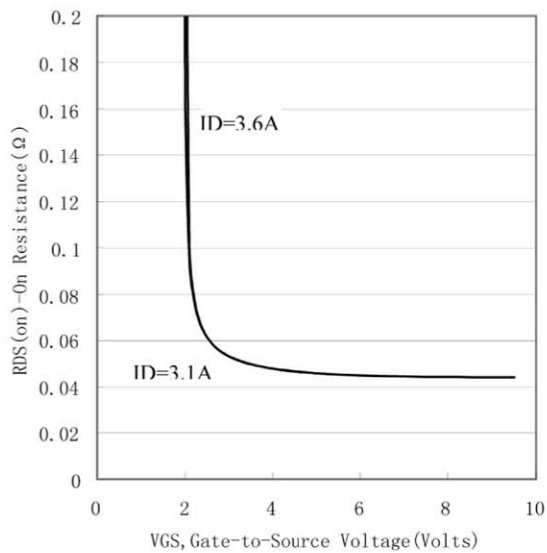
## Typical Characteristics



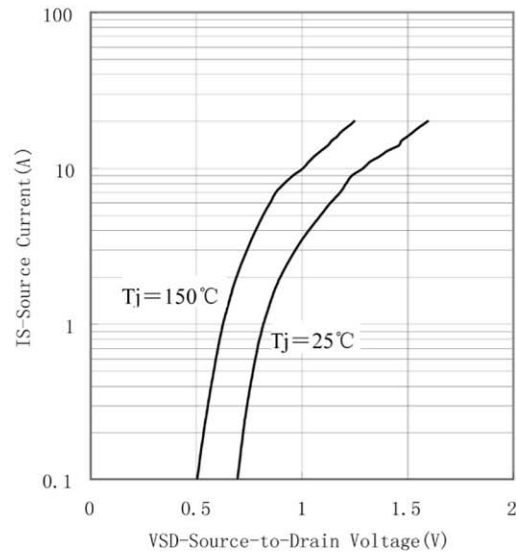
**Figure 5. On-Resistance Variation with Temperature**



**Figure 6. On-Resistance vs. Drain Current**



**Figure 7. On-Resistance vs. Gate-to-Source Voltage**



**Figure 8. Source-Drain Diode Forward Voltage**

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